FORM PTO-1449 US Dept. of Commerce Patent and Tradem ATTORNEY DOCKET NO. SERIAL NO. ATM1-661 10/618,024 APPLICANT INFORMATION DISCLOSURE STATEMENT Robert P. Vaudo, et al. (use several sheets if necessary) **FILING DATE** GROUP July 11, 2003 TBA U.S. PATENT DOCUMENTS **EXAMINER** PATENT FILING INITIAL NUMBER ISSUE DATE NAME CLASS SUBCLASS /PUBLICATION DATE IF APPROPRIATE 6,273,948 B1 8/14/2001 Porowski, et al. AB 5,385,862 1/31/1995 Moustakas AC 6,544,867 B1 4/8/2003 Webb, et al. \overline{AD} 5,686,738 11/7/1997 Moustakas AE 6,261,931 B1 7/17/2001 Keller, et al. AF US 7/25/2002 NAKAMWEA et al. 2002/0096692 257 194 FOREIGN PATENT DOCUMENTS DOCUMENT PUBLICATION TRANSLATION NUMBER DATE COUNTRY CLASS **SUBCLAS** YES (abstract only) OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.) Jerzy M. Langer, et al. "Transition-metal impurities in semiconductor and heterojunction band lineups". Physical Review B, Vol. 38, No. 11, pgs. 7723-7739, 15 Oct. 1988.

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